

## Product Summary

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>A</sub> = +25°C
40V	11.5mΩ @ V <sub>GS</sub> = 10V	11.6A
	18mΩ @ V <sub>GS</sub> = 4.5V	9.3A

## Description

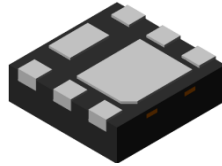
This new generation MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high efficiency power management applications:

- Power Management Functions
- DC-DC Converters
- Backlighting

U-DFN2020-6 (SWP) (Type F)



Top View



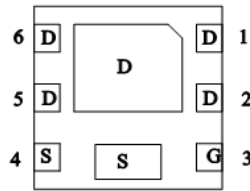
Bottom View

## Features

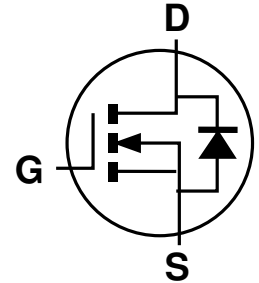
- Rated to +175°C – Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching, Test in Production – Ensures More Reliable and Robust End Application
- Low R<sub>DS(ON)</sub> – Ensures On State Losses Are Minimized
- 0.6mm Profile – Ideal for Low Profile Applications
- PCB Footprint of 4mm<sup>2</sup>
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. “Green” Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **An Automotive-Compliant Part is Available Under Separate Datasheet ([DMTH4008LDFWQ](#))**

## Mechanical Data

- Case: U-DFN2020-6 (SWP) (Type F)
- Case Material: Molded Plastic, “Green” Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208 (e3)
- Weight: 0.007 grams (Approximate)



Pin Out  
Bottom View



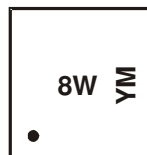
Internal Schematic

## Ordering Information (Note 4)

Part Number	Case	Quantity Per Reel
DMTH4008LDFW-7	U-DFN2020-6 (SWP) (Type F)	3,000
DMTH4008LDFW-13	U-DFN2020-6 (SWP) (Type F)	10,000

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, “Green” and Lead-free.
  3. Halogen- and Antimony-free “Green” products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information



8W = Product Type Marking Code  
 YM = Date Code Marking  
 Y = Year (ex: F = 2018)  
 M = Month (ex: 9 = September)

### Date Code Key

Year	2017	2018	2019	2020	2021	2022	2023	2024
Code	E	F	G	H	I	J	K	L

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DSS</sub>	40	V
Gate-Source Voltage	V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 7) V <sub>GS</sub> = 10V	I <sub>D</sub>	T <sub>A</sub> = +25°C	11.6
		T <sub>A</sub> = +100°C	8.2
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	80	A
Continuous Source-Drain Diode Current (Note 7)	I <sub>S</sub>	2.55	A
Pulsed Source-Drain Diode Current (10µs Pulse, Duty Cycle = 1%)	I <sub>SM</sub>	80	A
Avalanche Current, L = 0.3mH (Note 8)	I <sub>AS</sub>	14.7	A
Avalanche Energy, L = 0.3mH (Note 8)	E <sub>AS</sub>	32.4	mJ

**Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P <sub>D</sub>	0.99	W
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>θJA</sub>	153	°C/W
Total Power Dissipation (Note 6)	P <sub>D</sub>	2.35	W
Thermal Resistance, Junction to Ambient (Note 6)	R <sub>θJA</sub>	64.5	°C/W
Thermal Resistance, Junction to Case (Note 7)	R <sub>θJC</sub>	14.8	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +175	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b> (Note 9)						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	40	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250µA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	1	µA	V <sub>DS</sub> = 32V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS</b> (Note 9)						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1	1.7	3	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250µA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	9.1	11.5	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 10A
			12.9	18		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 8.5A
Diode Forward Voltage	V <sub>SD</sub>	—	0.8	1.0	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 10A
<b>DYNAMIC CHARACTERISTICS</b> (Note 10)						
Input Capacitance	C <sub>iss</sub>	—	1030	—	pF	V <sub>DS</sub> = 20V, V <sub>GS</sub> = 0V, f = 1MHz
Output Capacitance	C <sub>oss</sub>	—	324	—		
Reverse Transfer Capacitance	C <sub>rss</sub>	—	27	—		
Gate Resistance	R <sub>g</sub>	—	1.82	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Q <sub>g</sub>	—	6.8	—	nC	V <sub>DD</sub> = 20V, I <sub>D</sub> = 10A
Total Gate Charge (V <sub>GS</sub> = 10V)	Q <sub>g</sub>	—	14.2	—		
Gate-Source Charge	Q <sub>gs</sub>	—	2.0	—		
Gate-Drain Charge	Q <sub>gd</sub>	—	2.7	—		
Turn-On Delay Time	t <sub>D(ON)</sub>	—	3.1	—	ns	V <sub>DD</sub> = 20V, V <sub>GS</sub> = 10V, R <sub>g</sub> = 6Ω, I <sub>D</sub> = 10A
Turn-On Rise Time	t <sub>R</sub>	—	3.1	—		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	14.2	—		
Turn-Off Fall Time	t <sub>F</sub>	—	5.8	—		
Reverse Recovery Time	t <sub>RR</sub>	—	19.6	—	ns	I <sub>F</sub> = 10A, di/dt = 100A/µs
Reverse Recovery Charge	Q <sub>RR</sub>	—	8.2	—	nC	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
  - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
  - Thermal resistance from junction to soldering point (on the exposed drain pad).
  - I<sub>AS</sub> and E<sub>AS</sub> ratings are based on low frequency and duty cycles to keep T<sub>J</sub> = +25°C.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to product testing.

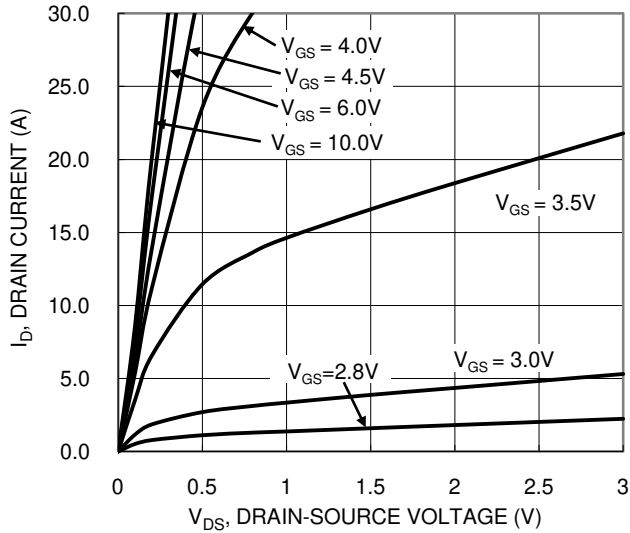


Figure 1. Typical Output Characteristic

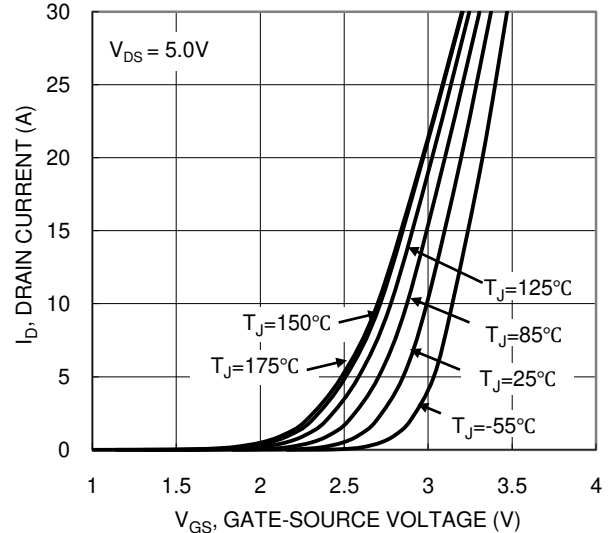


Figure 2. Typical Transfer Characteristic

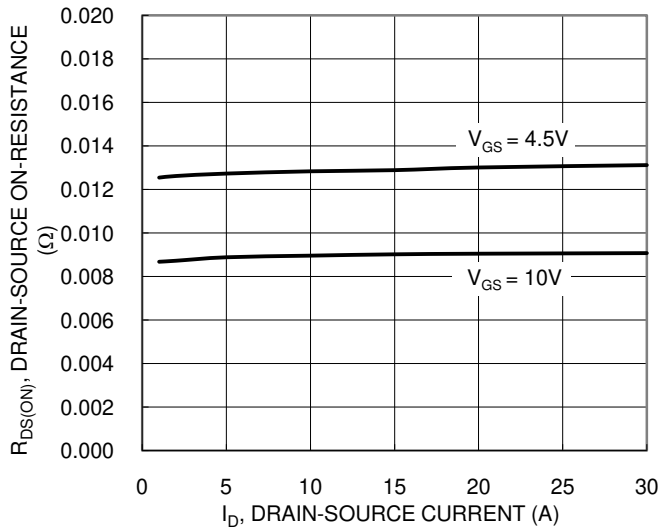


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

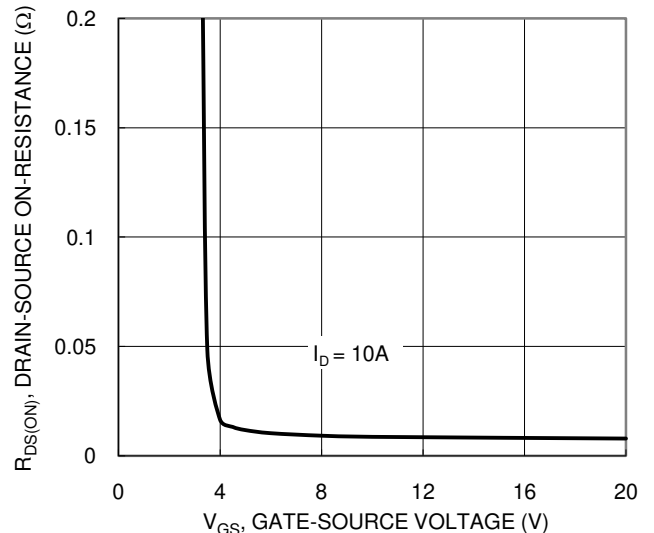


Figure 4. Typical Transfer Characteristic

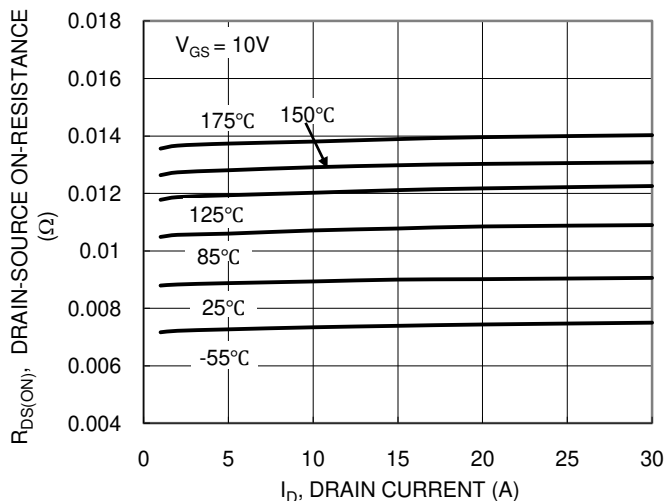


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

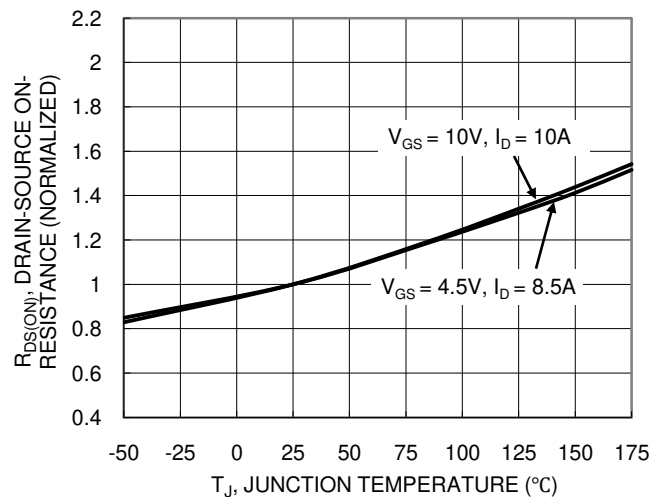


Figure 6. On-Resistance Variation with Temperature

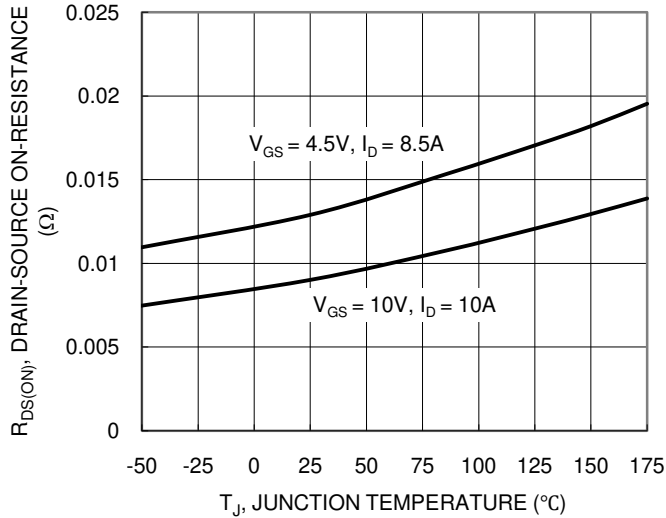


Figure 7. On-Resistance Variation with Temperature

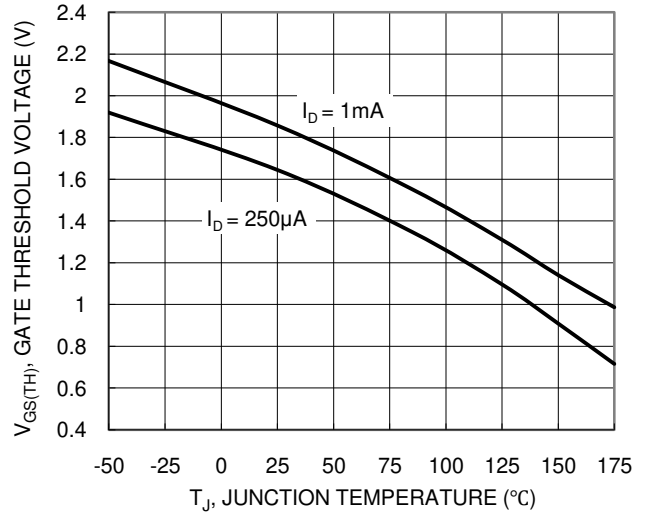


Figure 8. Gate Threshold Variation vs. Junction Temperature

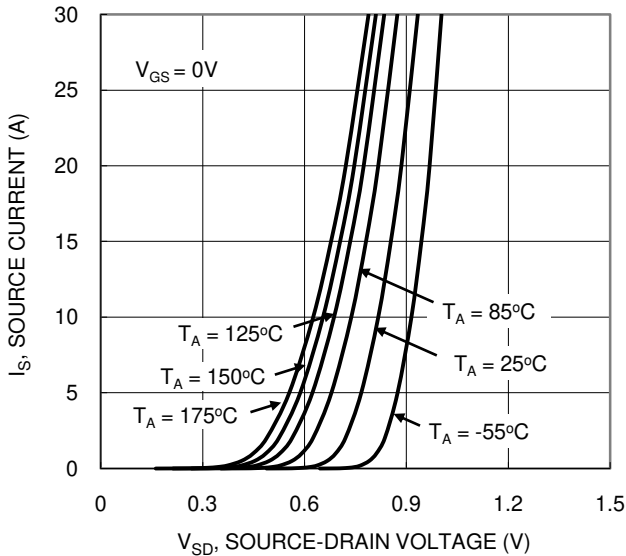


Figure 9. Diode Forward Voltage vs. Current

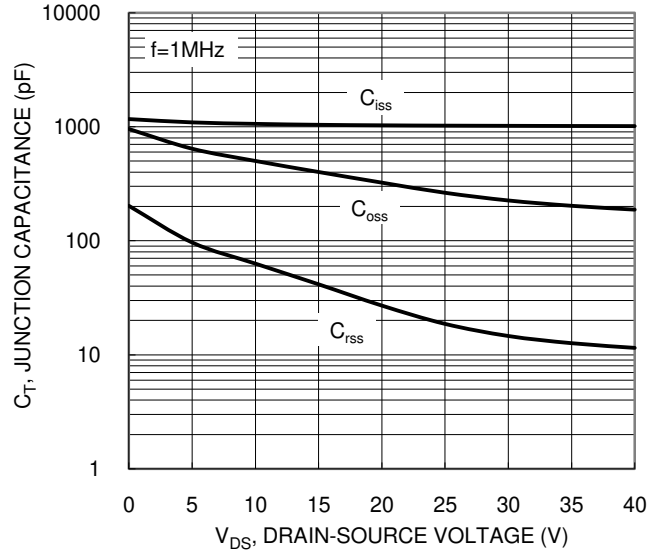


Figure 10. Typical Junction Capacitance

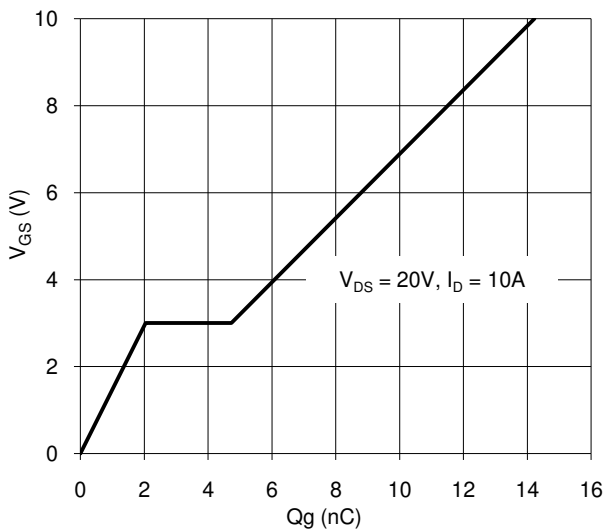


Figure 11. Gate Charge

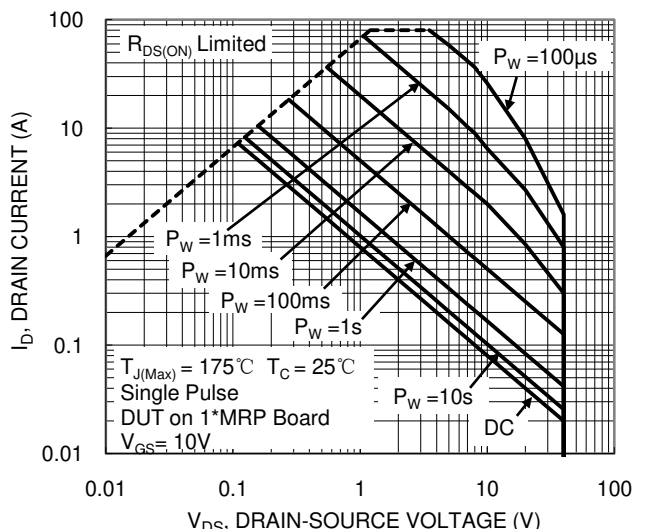


Figure 12. SOA, Safe Operation Area

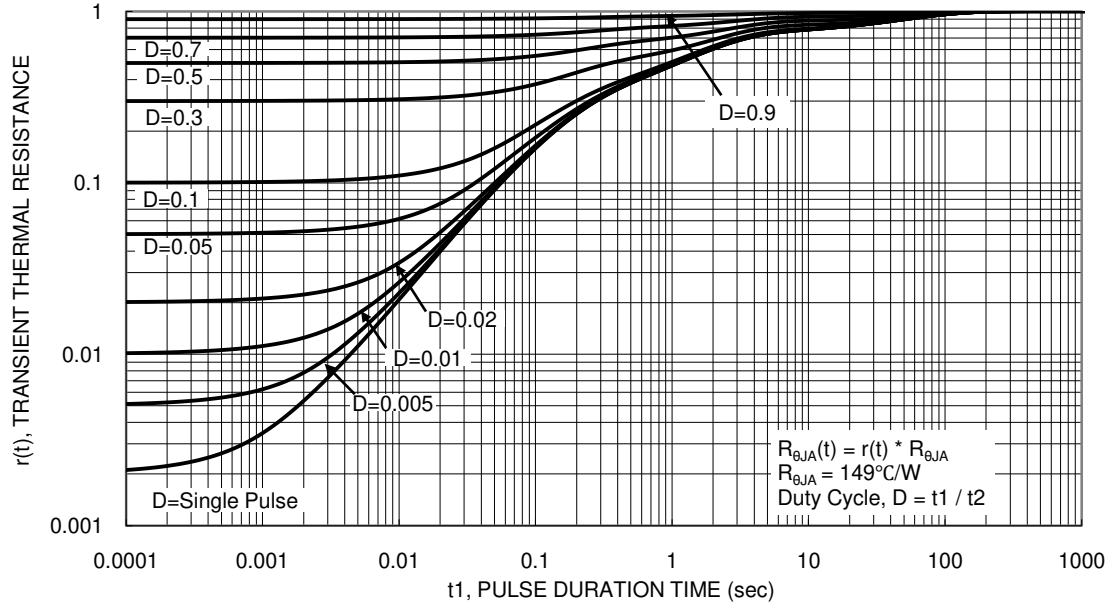
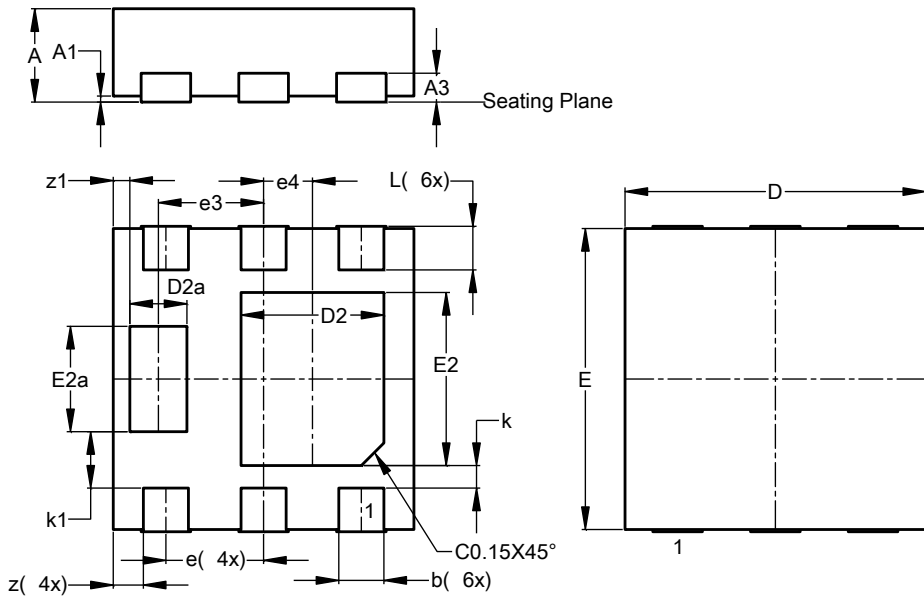


Figure 13. Transient Thermal Resistance

**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**U-DFN2020-6 (SWP) (Type F)**

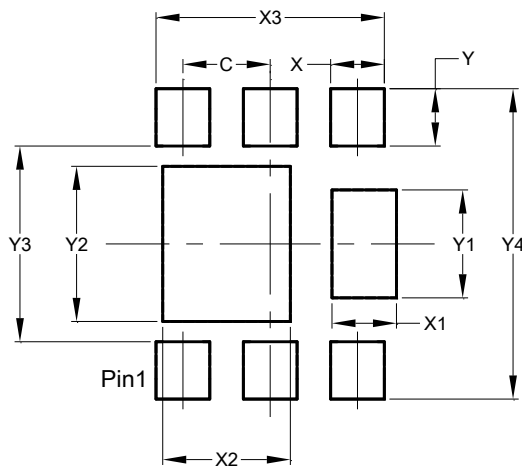


U-DFN2020-6 (SWP) (Type F)			
Dim	Min	Max	Typ
A	0.59	0.65	0.62
A1	0.00	0.05	0.03
A3	-	-	0.192
b	0.28	0.38	0.33
D	1.95	2.05	2.00
D2	0.87	1.07	0.97
D2a	0.35	0.45	0.40
E	1.95	2.05	2.00
E2	1.07	1.27	1.17
E2a	0.67	0.77	0.72
e	0.65 BSC		
e3	0.70 BSC		
e4	0.325 BSC		
k	--	--	0.15
k1	--	--	0.375
L	0.225	0.355	0.305
z	--	--	0.20
z1	--	--	0.11
<b>All Dimensions in mm</b>			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**U-DFN2020-6 (SWP) (Type F)**



Dimensions	Value (in mm)
C	0.650
X	0.400
X1	0.480
X2	0.950
X3	1.700
Y	0.425
Y1	0.800
Y2	1.150
Y3	1.450
Y4	2.300

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